G. Device & Process Modeling, Simulation and Reliability 분과

Room G
하나스퀘어 (B112)

일 시 : 2월 17일(금) 15:30-16:45
세션명 : [FG4-G] Device Characterization
좌 장 : 이상기(동부하이텍), 조인욱(하이닉스반도체)

FG4-G-1 15:30-16:00
[Invited]Low-frequency Noise in Precision Analog Components
저자: Badih El-Kareh
소속: Dongbu HiTek

FG4-G-2 16:30-16:45
Active Layer Thickness-dependent Parasitic Resistance Effect in Low Frequency Noise with Subgap Density-of-states in Amorphous Indium-gallium-zinc-oxide TFTs
저자: Hagyoul Bae, Dongsik Kong, Ja Sun Shin, Dayeon Yun, Euiyeon Hong, Hyojoon Seo, Hyunjun Choi, Jieun Lee, Hyun-Kwang Jung, Minkyung Bae, Yongsik Kim, Woojoon Kim, Dae Hwan Kim, and Dong Myong Kim
소속: School of Electrical Engineering, Kookmin University

FG4-G-3 16:00-16:15
Differential Ideality Factor Technique and Extraction of Subgap Density-of-states in Amorphous InGaZnO Thin-Film Transistors
저자: Minkyung Bae, Daeyoun Yun, Yongsik Kim, Dongsik Kong, Hyunkwang Jeong, Jaeman Jang, Woojoon Kim, Inseok Hur, Jaehyeong Kim, Yun Hyeok Kim, Jaewook Lee, Sungwoo Jun, Choon Hyeong Jo, Dae Hwan Kim, and Dong Myong Kim
소속: School of Electrical Engineering, Kookmin University

FG4-G-4 16:15-16:30
Characterization of Intrinsic Field Effect Mobility in a-IGZO Thin-film Transistors through the De-embedding the Parasitic Source and Drain Resistance Effects
저자: Inseok Hur, Hagyoul Bae, Minkyung Bae, Yongsik Kim, Dongsik Kong, Hyunkwang Jeong, Jaeman Jang, Jaehyeong Kim, Woojoon Kim, Yun Hyeok Kim, Jaewook Lee, Sungwoo Jun, Choon Hyeong Jo, Dong Myong Kim, and Dae Hwan Kim
소속: School of Electrical Engineering, Kookmin University